# **MOSFET** - Dual, N-Channel, **Small Signal**

# 20 V, 540 mA

#### **Features**

- Low R<sub>DS(on)</sub> Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- ESD Protected Gate
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## **Applications**

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

#### **MAXIMUM RATINGS** (T<sub>.1</sub> = 25°C unless otherwise noted.)

Paramet	Symbol	Value	Unit		
Drain-to-Source Voltage	V <sub>DSS</sub>	20	V		
Gate-to-Source Voltage			$V_{GS}$	±7.0	V
Continuous Drain Current	Steady	Steady T <sub>A</sub> = 25°C		540	mA
(Note 1)	State	$T_A = 85^{\circ}C$	I <sub>D</sub>	390	
Power Dissipation (Note 1)	Stea	dy State	P <sub>D</sub>	250	mW
Continuous Drain Current (Note 1)	t ≤ 5 s	$T_A = 25^{\circ}C$	I <sub>D</sub>	570	mA
(Note 1)	1 3 0 3	$T_A = 85^{\circ}C$	טי	410	
Power Dissipation (Note 1)	t:	≤ 5 s	P <sub>D</sub>	280	mW
Pulsed Drain Current	I <sub>DM</sub>	1.5	Α		
Operating Junction and Sto	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	ô		
Source Current (Body Diode	IS	350	mA		
Lead Temperature for Solde (1/8" from case for 10 s)	$T_L$	260	Ĉ		

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{ heta JA}$	500	°C/W
Junction-to-Ambient – $t \le 5$ s (Note 1)		447	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

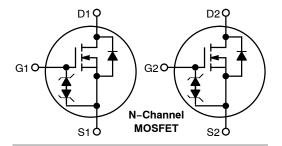
1. Surface mounted on FR4 board using 1 in sq pad size (Cu. area = 1.127 in sq [1 oz] including traces).



# ON Semiconductor®

#### www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Typ	I <sub>D</sub> Max (Note 1)		
	400 mΩ @ 4.5 V			
20	500 mΩ @ 2.5 V	540 mA		
	700 mΩ @ 1.8 V			



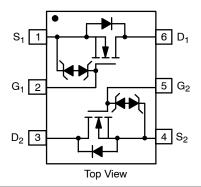


TV = Specific Device Code

= Date Code Μ = Pb-Free Package

(Note: Microdot may be in either location)

#### PINOUT: SOT-563



#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted.)

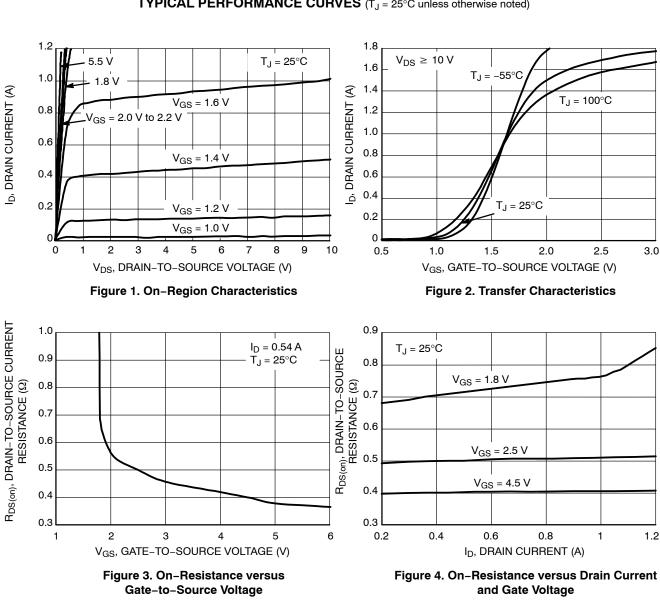
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit	
OFF CHARACTERISTICS	•							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20	_	_	V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	-	<del>-</del>		14	-	mV/°C	
Zero Gate Voltage Drain Current	ent V <sub>GS</sub> = 0 V		T <sub>J</sub> = 25°C	-	_	1.0	μΑ	
	I <sub>DSS</sub>	V <sub>DS</sub> = 16 V	T <sub>J</sub> = 125°C	-	_	5.0	1	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±	4.5 V	-	-	±5.0	μΑ	
ON CHARACTERISTICS (Note 3)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 25	0 μΑ	0.45	_	1.0	V	
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>	-		-	2.0	-	mV/°C	
Drain-to-Source On Resistance		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 54	0 mA	-	0.4	0.55	Ω	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 50	0 mA	-	0.5	0.7		
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 350 mA			0.7	0.9		
Forward Transconductance	9FS	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 540 mA			1.0	_	S	
CHARGES AND CAPACITANCES	•			•	•			
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = 16 V		-	80	150	pF	
Output Capacitance	C <sub>OSS</sub>			-	13	25	1	
Reverse Transfer Capacitance	C <sub>RSS</sub>			-	10	20		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V; I <sub>D</sub> = 540 mA		-	1.5	2.5	nC	
Threshold Gate Charge	Q <sub>G(TH)</sub>			-	0.1	-		
Gate-to-Source Charge	Q <sub>GS</sub>			-	0.2	-	1	
Gate-to-Drain Charge	$Q_{GD}$			-	0.35	-		
SWITCHING CHARACTERISTICS, $V_{GS} = V$	Note 4)							
Turn-On Delay Time	t <sub>d(ON)</sub>			-	6.0	-	ns	
Rise Time	t <sub>r</sub>	$V_{GS}$ = 4.5 V, $V_{DD}$ = 10 V, $I_{D}$ = 540 mA, $R_{G}$ = 10 $\Omega$		-	4.0	-		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			-	16	-		
Fall Time	t <sub>f</sub>	<u> </u>			8.0	-		
DRAIN-SOURCE DIODE CHARACTERISTIC	cs							
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V,	T <sub>J</sub> = 25°C	-	0.7	1.2	V	
		I <sub>S</sub> = 350 mA	T <sub>J</sub> = 125°C	-	0.6	-		
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V}, d_{ISD}/d_t = 100 \text{ A}/\mu \text{s}$	s, I <sub>S</sub> = 350 mA	-	6.5	_	ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Surface–mounted on FR4 board using 1 in. sq. pad size (Cu. area = 1.127 in sq [1 oz] including traces).

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
   Switching characteristics are independent of operating junction temperatures.

## TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise noted)



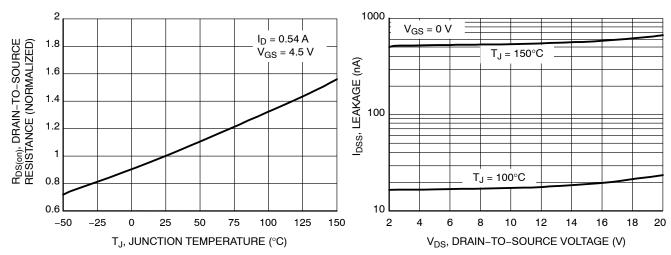
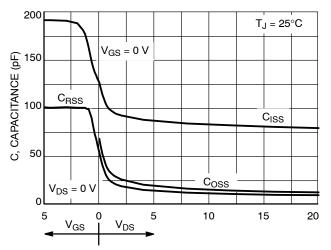


Figure 5. On-Resistance Variation with **Temperature** 

Figure 6. Drain-to-Source Leakage Current versus Voltage

# TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise noted)



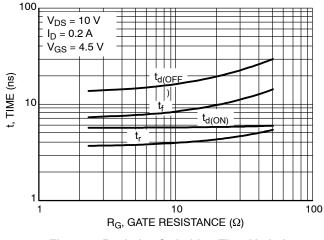
 $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$  OPAIN–TO–SOURCE VOLTAGE (V) V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (V)  $V_{DS}$  $V_{GS}$  $Q_{GS}$  $Q_{GD}$  $I_D = 0.54 A$  $T_J = 25^{\circ}C$ 0 0.2 0 0.4 0.6 0.8 1.2 1.4 1.6 Qg, TOTAL GATE CHARGE (nC)

 $\mathsf{Q}_\mathsf{T}$ 

GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (V)

Figure 8. Gate-to-Source and **Drain-to-Source Voltage versus Total Charge** 





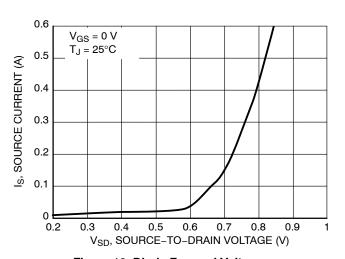


Figure 9. Resistive Switching Time Variation versus Gate Resistance

Figure 10. Diode Forward Voltage versus Current

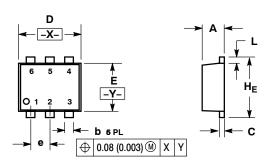
#### **ORDERING INFORMATION**

Device	Package	Shipping		
NTZD3154NT1G				
NTZD3154NT1H		4000 / Taga & Basil		
NTZD3154NT2G	SOT-563	4000 / Tape & Reel		
NTZD3154NT2H	(Pb-Free)			
NTZD3154NT5G		0000 / Tana & Daal		
NTZD3154NT5H		8000 / Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

#### SOT-563, 6 LEAD CASE 463A **ISSUE F**

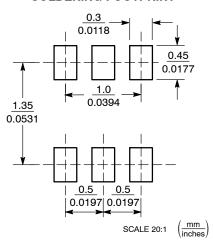


#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- JUNEAU DINING AND FOLL FARMING FELL MANN
  714.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETERS
  MAXIMUM LEAD THICKNESS INCLUDES LEAD
  FINISH THICKNESS. MINIMUM LEAD THICKNESS
  IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MIL	LIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
Е	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC			0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
He	1.50	1.60	1.70	0.059	0.062	0.066	

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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